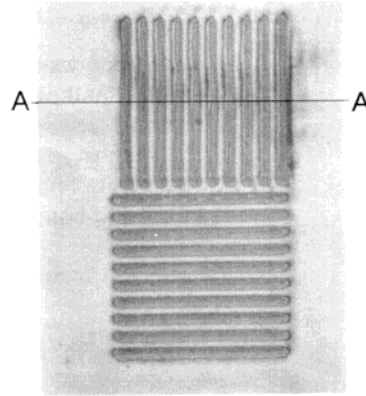
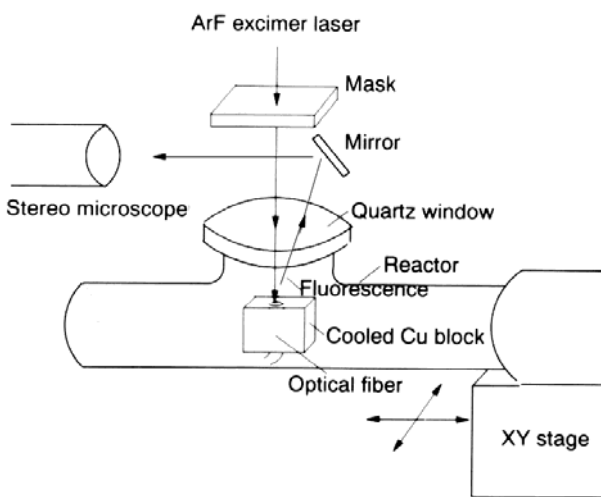
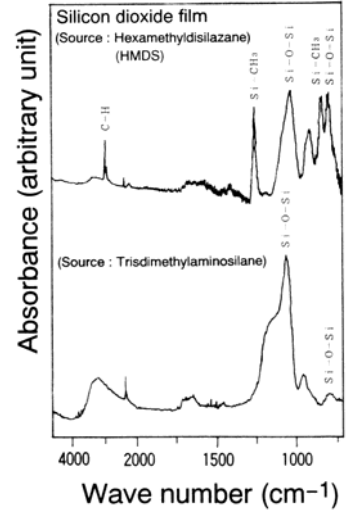


# レーザープロセスとステルスダイシング

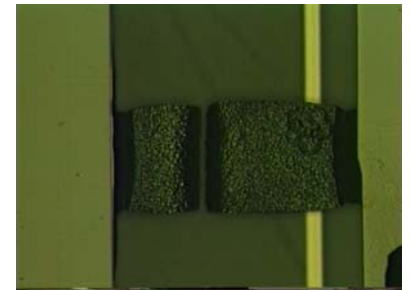
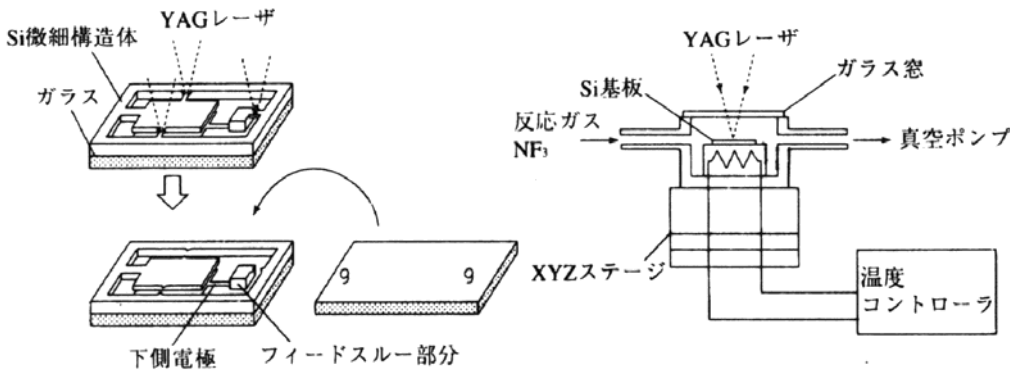


Pressure of HMDS : 470Pa  
 Pressure of O<sub>2</sub> : 67Pa  
 Substrate temp. : 2°C  
 Laser irradiation time : 2min



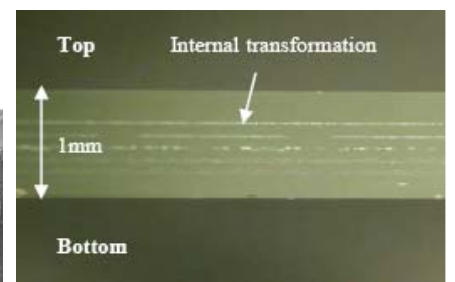
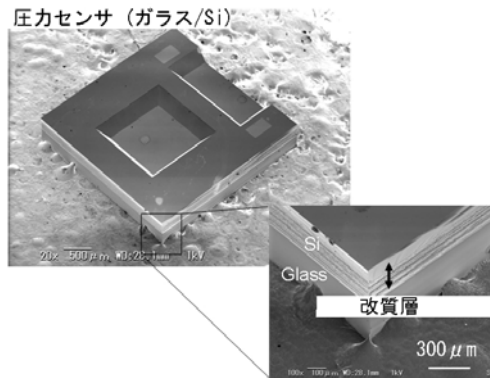
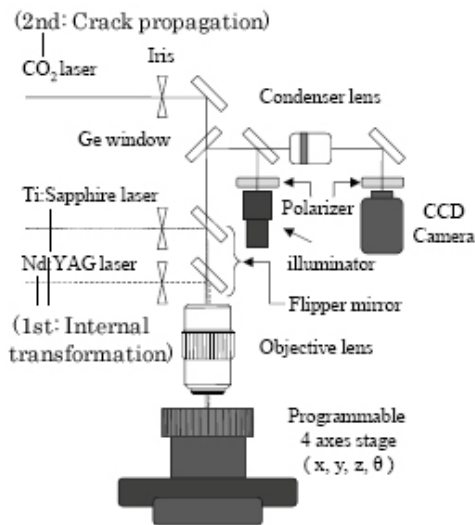
レーザープロジェクション CVD

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レーザー支援 Si エッチング

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Si-ガラス構造のレーザー(ステルス)ダイシング (東北大 - レーザ総研)

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